

3rd JST/CREST/2D Workshop in Singapore

Date: Friday 15 March 2019

Time: 16:00 to 19:00 hrs

Venue: Melati Junior Ballroom, Marina Bay Sands Convention Centre, Singapore

Registration fee: Free for 2019 EDTM registered participants

Technical Programme:

16:00 Greeting, Atsushi Kurobe, Toshiba

16:05 Keynote, Kaustav Banerjee, UCSB,
"2D Materials for Next-Generation LSI and IoT Devices"

16:35 Invited, Kah-Wee Ang, NUS
"Rediscovering black phosphorus layered material for electronic and optoelectronic device applications"

17:05 Manabu Ohtomo, Fujitsu,
"Bottom-up synthesis of edge-functionalized graphene nanoribbons for heterojunction devices"

17:25 Coffee Break

17:35 Yasumitsu Miyata, Tokyo Metropolitan Univ.,
"Semiconductor heterojunctions based on 2D materials"

17:55 Tomoki Machida, Institute of Industrial Science, University of Tokyo
"Robotic assembly and mid-infrared photoresponse of van der Waals junctions of graphene and 2D materials"

18:15 Atsushi Ogura / Yusuke Hibino, Meiji Univ.,
"Fabrication of various TMD materials with MOCVD and sputtering deposition"

19:35 Hitoshi Wakabayashi, Tokyo Tech,
"2D FET and Materials using Sputtering"

18:55 Closing remarks, Hitoshi Wakabayashi, Tokyo Tech

19:00 Adjourn

This workshop is sponsored by JST and technically supported by 2019 EDTM.